

Figure 1

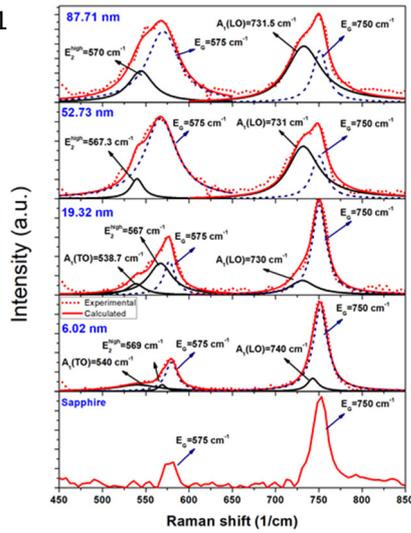


Figure 2

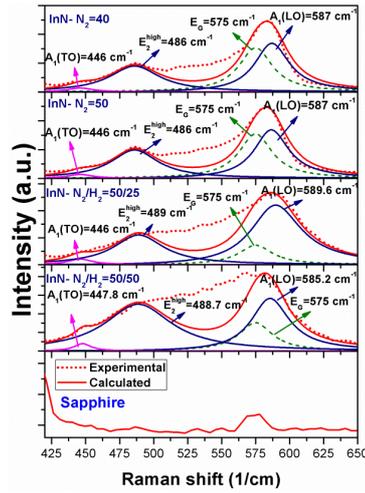


Figure 3

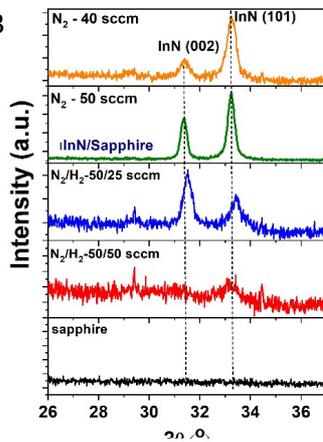


Figure 4

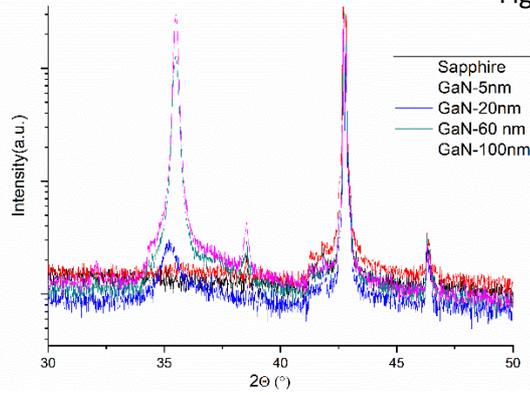


Figure 5

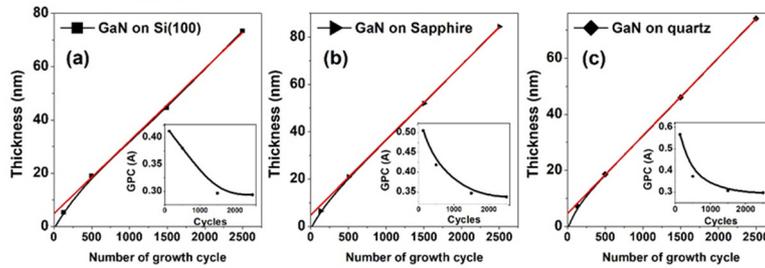


Figure 1 Evolution of Raman spectra for GaN films on Sapphire with different thickness

Figure 2 Evolution of Raman spectra for GaN films on Sapphire with different N_2/H_2 plasma flows

Figure 3 XRD spectra measured on InN films deposited on sapphire substrates using different plasma flows

Figure 4 XRD spectra measured on GaN films deposited on sapphire substrates with different thickness

Figure 5 Dependency of GPC on the substrate. Substrate-enhanced growth of (a) GaN on Si(100) (b) GaN on sapphire, and (c) GaN on quartz with different thicknesses grown by HCPA-ALD.